



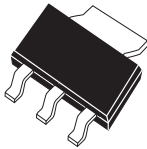
CZS5064

SILICON CONTROLLED RECTIFIER

CentralTM
Semiconductor Corp.

DESCRIPTION

The CENTRAL SEMICONDUCTOR CZS5064 type is an epoxy molded PNP Silicon Controlled Rectifier manufactured in an epoxy molded surface mount package, designed for control systems and sensing circuit applications.



SOT-223 CASE

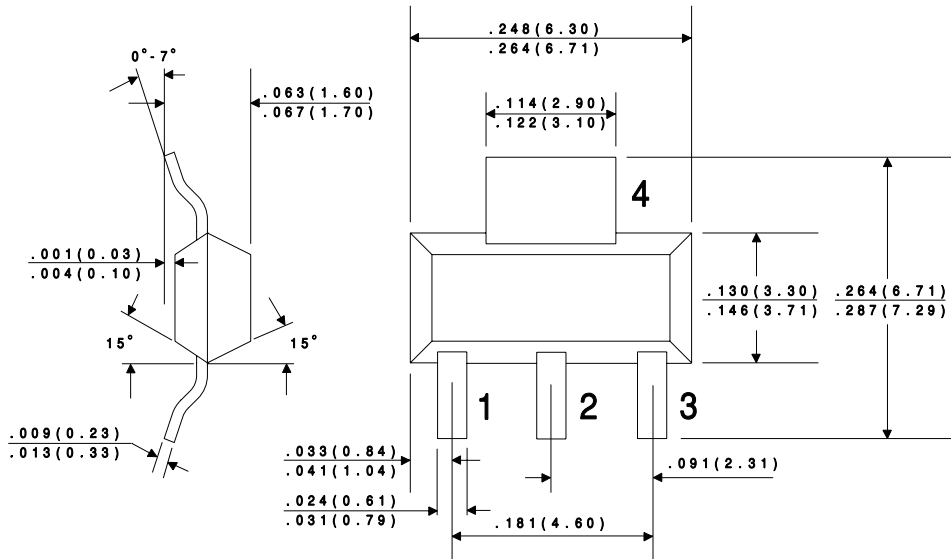
MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

	SYMBOL		UNITS
Peak Repetitive Off-State Voltage	V_{DRM}	400	V
Peak Repetitive Reverse Voltage	V_{RRM}	400	V
RMS On-State Current	$I_T(\text{RMS})$	0.8	A
Average On-State Current ($T_C=67^{\circ}\text{C}$)	$I_T(\text{AV})$	0.51	A
Operating Junction Temperature	T_J	-40 to +125	$^{\circ}\text{C}$
Storage Temperature	T_{stg}	-40 to +150	$^{\circ}\text{C}$
Thermal Resistance	θ_{JA}	150	$^{\circ}\text{C}/\text{W}$
Thermal Resistance	θ_{JC}	25	$^{\circ}\text{C}/\text{W}$

ELECTRICAL CHARACTERISTICS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_{DRM}	$V_D=400\text{V}, R_{GK}=1\text{K}\Omega, T_C=125^{\circ}\text{C}$		50	μA
I_{RRM}	$V_D=400\text{V}, R_{GK}=1\text{K}\Omega, T_C=125^{\circ}\text{C}$		50	μA
V_T	$I_T=1.2\text{A}$		1.7	V
I_{GT}	$V_D=7.0\text{V}, R_L=100\Omega, R_{GK}=1\text{K}\Omega$		200	μA
V_{GT}	$V_D=7.0\text{V}, R_L=100\Omega, R_{GK}=1\text{K}\Omega$		0.8	V
V_{GD}	$V_D=400\text{V}, R_L=100\Omega, T_C=125^{\circ}\text{C}$	0.1		V
I_H	$V_D=7.0, R_{GK}=1\text{K}\Omega$		5.0	mA
t_{ON}	$V_D=400\text{V}, I_{GT}=1.0\text{mA}, I_F=1.0\text{A}, R_{GK}=1.0\Omega, di/dt=6.0\text{A}/\mu\text{s}$		2.8 TYP	μs

All dimensions in inches (mm).



LEAD CODE:

- 1) CATHODE
- 2) ANODE
- 3) GATE
- 4) ANODE